

Abstract of the Disclosure

The present invention is related to a ferroelectric memory device and a method for fabricating the same. The
5 ferroelectric memory device includes: a substrate providing a transistor; a first insulation material with a plane surface formed on the substrate; a storage node contact passing through the first insulation material to contact to an active region of the substrate; a lower electrode being connected to
10 the storage node contact and including a solid solution layer disposed at least as an upper most layer, the solid solution layer being doped with a metal element, which is induced to be in a solid solution state; a second insulation material having a plane surface that exposes a surface of the lower electrode,
15 encompassing the lower electrode and being formed on the first insulation material; a ferroelectric layer covering the second insulation material including the lower electrode; an upper electrode formed on the ferroelectric layer.